

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-26 (Canceled).

Claim 27 (New): A correction method for correction of an erroneous design made in a first thin layer including at least one first engraved sub-layer including the erroneous design and at least one second sub-layer located between a substrate and the first sub-layer, the method comprising:

- a) depositing a second thin layer on the first thin layer;
- b) engraving or lithography of the second thin layer, as a function of a desired correction or corrections; and
- c) etching the second sub-layer through the first sub-layer.

Claim 28 (New): A correction method as claimed in claim 27, the desired correction including an addition of one or more patterns.

Claim 29 (New): A correction method as claimed in Claim 27, in which one or more patterns are missing from the design, the engraving or lithography including reproduction in the second thin layer of the missing patterns.

Claim 30 (New): A correction method as claimed in Claim 27, further comprising d) etching the first sub-layer through the second thin layer after the engraving or lithography b) and prior to the etching c).

Claim 31 (New): A correction method as claimed in claim 30, further comprising removing the second thin layer after the etching d) of the first sub-layer through the second thin layer and prior to the etching c).

Claim 32 (New): A correction method as claimed in Claim 27, the correction including removing one or more patterns.

Claim 33 (New): A correction method as claimed in Claim 32, in which the one or more patterns are in excess, the engraving or lithography in the second thin layer leaving one or more blocks filling the patterns in excess.

Claim 34 (New): A correction method as claimed in Claim 27, the correction including adding one or more missing patterns, then eliminating one or more other patterns in excess.

Claim 35 (New): A correction method as claimed in Claim 34, further comprising, after the engraving or lithography b) and prior to the engraving c):

etching the first sub-layer through the second thin layer;

removing the second thin layer;

depositing a third thin layer on the first sub-layer; and

second lithography in the third thin layer leaving blocks filling the patterns in excess.

Claim 36 (New): A correction method as claimed in Claim 35, the third thin layer being a dielectric layer.

Claim 37 (New): A correction method as claimed in Claim 36, the third thin layer being a resin or polymer layer.

Claim 38 (New): A correction method as claimed in Claim 35, the third thin layer being a positive or negative photosensitive resin layer.

Claim 39 (New): A correction method as claimed in Claim 35, further comprising removing the third thin layer after the etching c).

Claim 40 (New): A correction method as claimed in Claim 27, further comprising removing the first sub-layer after the etching c) of the second sub-layer through the first sub-layer.

Claim 41 (New): A correction method as claimed in Claim 27, in which the first sub-layer is based on a first conductive, or semiconductive, or insulating material, and the second sub-layer located between the substrate and the first sub-layer is based on a second conductive, or semiconductive, or insulating material different from the first material.

Claim 42 (New): A correction method as claimed in Claim 27, in which the first sub-layer is a sacrificial layer.

Claim 43 (New): A method for correction of an erroneous design made in a first thin layer, at least partially etched, comprising:

- a) depositing a second thin layer on the first thin layer;
- b) engraving or lithography in the second thin layer as a function of a desired correction; and
- c) etching the first thin layer through the second thin layer.

Claim 44 (New): A method as claimed in Claim 43, the engraving or lithography comprising reproducing the missing patterns in the second thin layer.

Claim 45 (New): A method as claimed in Claim 43, further comprising removing the second thin layer after the etching of the first thin layer through the second thin layer.

Claim 46 (New): A method as claimed in Claim 27, the second thin layer being a dielectric layer.

Claim 47 (New): A method as claimed in Claim 27, the second thin layer being a resin or polymer layer.

Claim 48 (New): A method as claimed in Claim 27, the engraving or lithography being carried out by direct writing.

Claim 49 (New): A method as claimed in Claim 27, the engraving or lithography being carried out by one or more optical particle beams.

Claim 50 (New): A method as claimed in Claim 49, the one or more optical particle beams being selected from among: an ion beam, an electron beam, a proton beam, an X-ray beam, a laser beam, an UV beam.

Claim 51 (New): A method as claimed in Claim 49, the beam being controlled by a digital device associated with a data medium including data relative to the erroneous design and to a desired corrected design.

Claim 52 (New): A lithography device carrying out one or more of the lithography of the method as claimed in Claim 27, comprising:

first means for producing at least one lithography beam;

second means for processing data relative to an erroneous design formed in a thin layer, and data relative to a desired corrected design, and for producing correction data following such processing; and

third means for controlling the first means, from correction data produced by the second means.